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FFB2227A / FMB2227A **NPN & PNP General-Purpose Amplifier**

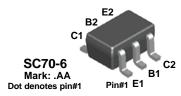
Description

This complementary device is a medium-power amplifier and switch, requiring collector currents up to 500 mA. Sourced from Process 19 and 63. See FFB2222A (NPN) and FFB2907A (PNP) for characteristics.

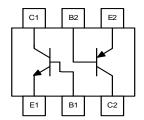
Ordering Information

Part Number	Top Mark	Package	Packing Method
FFB2227A	AA	SC70 6L	Tape and Reel
FMB2227A	001	SSOT 6L	Tape and Reel

Block Diagram



FFB2227A Device Package



FFR2227∆	Internal C	onnoction

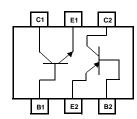
TRANSISTOR TYPE C1 B1 E1 C2 B2 E2

FMB2227A Device Package

SuperSOT™-6

Mark: .001

Dot denotes pin#1



FMB2227A Internal Connection

1

Absolute Maximum Ratings(1)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current - Continuous	500	mA
T _{J,} T _{STG}	Operating and Storage Junction Temperature Range	- 55 to +150	°C

Notes:

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or lowduty cycle operations.
- 3. All voltages (V) and currents (A) are negative polarity for PNP transistors.
- 4. These Ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics(2)

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Maxi	Units	
		FFB2227A	FMB2227A	Office
P _D	Total Device Dissipation	300	700	mV
	Derate Above 25°C	2.4	5.6	mV/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	415	180	°C/W

Note:

2. PCB board size: FR-4 76 x 114 x 0.6T mm³(3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics(3)

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
OFF CHAF	RACTERISTICS					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage ⁽⁴⁾	I _C = 10 mA, I _B = 0	30			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 10 μA, I _E = 0	60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5			V
I _{CBO}	Collector Cut-Off Current	V _{CB} = 50 V, I _E = 0			30	nA
I _{EBO}	Emitter Cut-Off Current	V _{EB} = 3.0 V, I _C = 0			30	nA
ON CHAR	ACTERISTICS					
	DC Current Gain	I _C = 1.0 mA, V _{CE} = 10 V	50			
h		I _C = 10 mA, V _{CE} = 10 V	75			
h _{FE}		I _C = 150 mA, V _{CE} = 10 V ⁽⁴⁾	100			
		I_C = 300 mA, V_{CE} = 10 $V^{(4)}$	30			
\/ (aat)	Collector-Emitter Saturation Voltage ⁽⁴⁾	I _C = 150 mA, I _B = 15 mA			0.4	V
V _{CE} (sat)		I _C = 300 mA, I _B = 30 mA			1.4	V
V _{BE} (sat)	Base-Emitter Saturation Voltage ⁽⁴⁾	I _C = 150 mA, I _B = 15 mA			1.3	V
SMALL SIG	SNAL CHARACTERISTICS					
f _T	Current Gain - Bandwidth Product	I _C = 50 mA, V _{CE} = 20 V, f = 100 MHz		250		MHz
C _{obo}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 100 kHz		4.0		pF
C _{ibo}	Input Capacitance	$V_{EB} = 2.0 \text{ V}, I_C = 0, f = 100 \text{ kHz}$		12		pF
NF	Noise Figure	I_C = 100 μA, V_{CE} = 10 V, R_S = 1.0 kΩ, f = 1.0 kHz		2.0		dB
SWITCHIN	G CHARACTERISTICS			•		
t _{on}	Turn-on Time			30		ns
t _d	Delay Time	$V_{CC} = 30 \text{ V, I}_{C} = 150 \text{ mA,}$ $I_{B1} = 15 \text{ mA}$		8.0		ns
t _r	Rise Time			20		ns
t _{off}	Turn-off Time	$V_{CC} = 6.0 \text{ V}, I_{C} = 150 \text{ mA},$ $I_{B1} = I_{B2} = 15 \text{ mA}$		80		ns
t _s	Storage Time			60		ns
t _f	Fall Time	ום: ושל וסיויי.		20		ns

- 3. All voltages (V) and currents (A) are negative polarity for PNP transistors.
- 4. Pulse test: pulse width \leq 300 μ s, duty cycle \leq 2.0%.

Physical Dimensions

SC70 6L

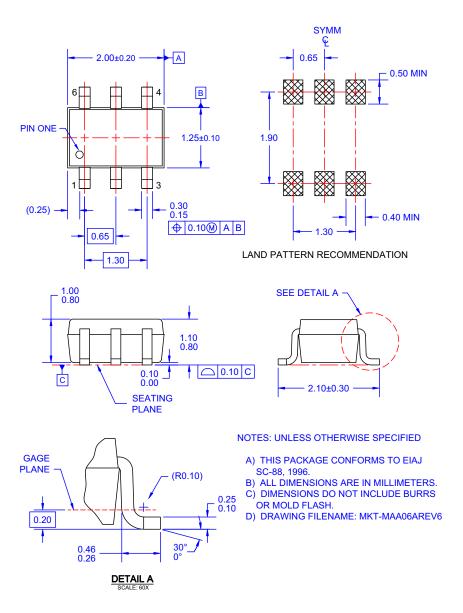


Figure 2. 6-LEAD, SC70, EIAJ SC-88, 1.25 MM WIDE (ACTIVE)

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Physical Dimensions (Continued)

SSOT 6L

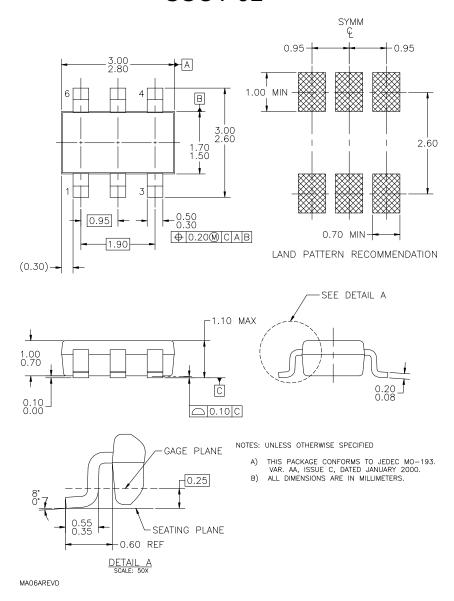


Figure 3. 6-LEAD, SUPER SOT-6, JEDEC MO-193, 1.6 MM WIDE (ACTIVE)

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